

Date: March 15<sup>th</sup>, 2021

GaN Etch Experiment #1

	Etch Rate	RIE Power	BCl <sub>3</sub> Gas	Pressure
Etch A	90 nm/min	100 W	21 sccm	7 mTorr
Etch B	130 nm/min	125 W	49 sccm	7 mTorr
Etch C	140 nm/min	150 W	55 sccm	7 mTorr
Etch D	200 nm/min	175 W	63 sccm	7 mTorr